# Dual 4-Stage Binary Ripple Counter with ÷ 2 and ÷ 5 Sections

## **High-Performance Silicon-Gate CMOS**

The MC74HC390A is identical in pinout to the LS390. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device consists of two independent 4-bit counters, each composed of a divide-by-two and a divide-by-five section. The divide-by-two and divide-by-five counters have separate clock inputs, and can be cascaded to implement various combinations of  $\div$  2 and/or  $\div$  5 up to a  $\div$  100 counter.

Flip-flops internal to the counters are triggered by high-to-low transitions of the clock input. A separate, asynchronous reset is provided for each 4-bit counter. State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used as clocks or strobes except when gated with the Clock of the HC390A.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No 7A
- Chip Complexity: 244 FETs or 61 Equivalent Gates
- Pb-Free Packages are Available\*



#### ON Semiconductor®

http://onsemi.com

#### MARKING DIAGRAMS

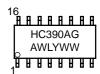


PDIP-16 N SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F





SOEIAJ-16 F SUFFIX CASE 966



A = Assembly Location

L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week
G = Pb-Free Package
■ Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

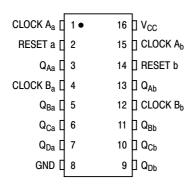


Figure 1. Pin Assignment

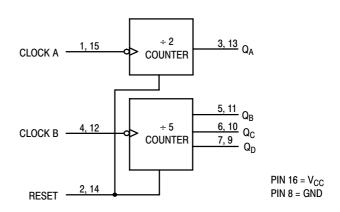


Figure 2. Logic Diagram

#### **FUNCTION TABLE**

Clo	ock		
Α	В	Reset	Action
Х	Χ	Н	Reset
			÷ 2 and ÷ 5
~	Χ	L	Increment
			÷ 2
Х	~	L	Increment
			÷ 5



#### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74HC390AN	PDIP-16	500 Units / Rail
MC74HC390ANG	PDIP-16 (Pb-Free)	500 Units / Rail
MC74HC390AD	SOIC-16	48 Units / Rail
MC74HC390ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC390ADR2	SOIC-16	2500 Units / Reel
MC74HC390ADR2G	SOIC-16 (Pb-Free)	2500 Units / Reel
MC74HC390ADTR2	TSSOP-16*	2500 Units / Reel
MC74HC390ADTR2G	TSSOP-16*	2500 Units / Reel
MC74HC390AF	SOEIAJ-16	50 Units / Rail
MC74HC390AFG	SOEIAJ-16 (Pb-Free)	50 Units / Rail
MC74HC390AFEL	SOEIAJ-16	2000 Units / Reel
MC74HC390AFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. \*This package is inherently Pb–Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	± 20	mA
I <sub>out</sub>	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected. †Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	<b>- 5</b> 5	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 1) $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 600 500 400	ns

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IH} \text{ or } V_{IL} &  I_{out}  \leq 2.4 \text{ mA} \\  I_{out}  \leq 4.0 \text{ mA} \\  I_{out}  \leq 5.2 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\label{eq:Vin} \begin{aligned} V_{in} = V_{IH} \text{ or } V_{IL} &   I_{out}  \leq 2.4 \text{ mA} \\ &   I_{out}  \leq 4.0 \text{ mA} \\ &   I_{out}  \leq 5.2 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	4	40	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### AC ELECTRICAL CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_f = t_f = 6 \text{ ns}$ )

			Gu	aranteed Li	mit	
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle)	2.0	10	9	8	MHz
	(Figures 1 and 3)	3.0	15	14	12	
		4.5	30	28	25	
		6.0	50	45	40	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Clock A to QA	2.0	70	80	90	ns
t <sub>PHL</sub>	(Figures 1 and 3)	3.0	40	45	50	
		4.5	24	30	36	
		6.0	20	26	31	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Clock A to QC	2.0	200	250	300	ns
t <sub>PHL</sub>	(QA connected to Clock B)	3.0	160	185	210	
	(Figures 1 and 3)	4.5	58	65	70	
		6.0	49	62	68	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Clock B to QB	2.0	70	80	90	ns
t <sub>PHL</sub>	(Figures 1 and 3)	3.0	40	45	50	
		4.5	26	33	39	
		6.0	22	28	33	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Clock B to QC	2.0	90	105	180	ns
t <sub>PHL</sub>	(Figures 1 and 3)	3.0	56	70	100	
		4.5	37	46	56	
		6.0	31	39	48	
t <sub>PLH</sub> ,	Maximum Propagation Delay, Clock B to QD	2.0	70	80	90	ns
t <sub>PHL</sub>	(Figures 1 and 3)	3.0	40	45	50	
		4.5	26	33	39	
		6.0	22	28	33	
t <sub>PHL</sub>	Maximum Propagation Delay, Reset to any Q	2.0	80	95	110	ns
	(Figures 2 and 3)	3.0	48	65	75	
		4.5	30	38	44	
		6.0	26	33	39	
t <sub>TLH</sub> ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t <sub>THL</sub>	(Figures 1 and 3)	3.0	27	32	36	
=		4.5	15	19	22	
		6.0	13	15	19	
C <sub>in</sub>	Maximum Input Capacitance	-	10	10	10	pF

<sup>1.</sup> For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>2.</sup> Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Counter)*	35	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

#### **TIMING REQUIREMENTS** (Input $t_r = t_f = 6 \text{ ns}$ )

			Gu	aranteed Li	mit	
Symbol	Parameter	v <sub>cc</sub> v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t <sub>rec</sub>	Minimum Recovery Time, Reset Inactive to Clock A or Clock B (Figure 2)	2.0 3.0 4.5 6.0	25 15 10 9	30 20 13 11	40 30 15 13	ns
t <sub>w</sub>	Minimum Pulse Width, Clock A, Clock B (Figure 1)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 15	110 36 22 19	ns
t <sub>w</sub>	Minimum Pulse Width, Reset (Figure 2)	2.0 3.0 4.5 6.0	75 27 20 18	95 32 24 22	110 36 30 28	ns
t <sub>f</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times (Figure 1)	2.0 3.0 4.5 6.0	1000 800 500 400	1000 800 500 400	1000 800 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### **PIN DESCRIPTIONS**

## INPUTS Clock A (Pins 1, 15) and Clock B (Pins 4, 15)

Clock A is the clock input to the ÷ 2 counter; Clock B is the clock input to the ÷ 5 counter. The internal flip—flops are toggled by high-to-low transitions of the clock input.

#### CONTROL INPUTS Reset (Pins 2, 14)

Asynchronous reset. A high at the Reset input prevents counting, resets the internal flip-flops, and forces  $Q_A$  through  $Q_D$  low.

#### OUTPUTS Q<sub>A</sub> (Pins 3, 13)

Output of the  $\div$  2 counter.

#### Q<sub>B</sub>, Q<sub>C</sub>, Q<sub>D</sub> (Pins 5, 6, 7, 9, 10, 11)

Outputs of the  $\div$  5 counter.  $Q_D$  is the most significant bit.  $Q_A$  is the least significant bit when the counter is connected for BCD output as in Figure 4.  $Q_B$  is the least significant bit when the counter is operating in the bi–quinary mode as in Figure 5.

#### **SWITCHING WAVEFORMS**

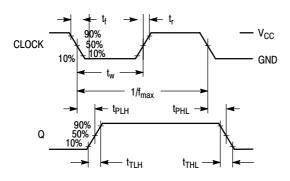


Figure 3.

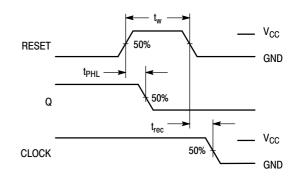
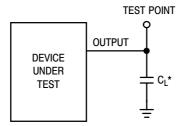


Figure 4.

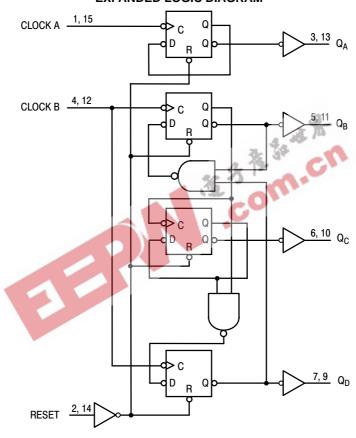
#### **TEST CIRCUIT**



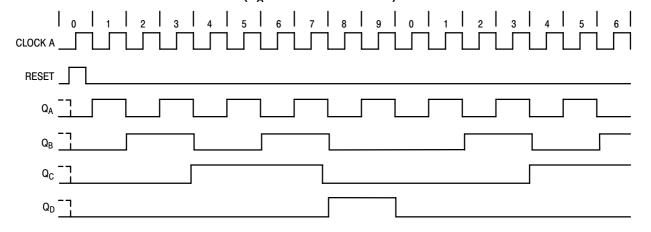
\*Includes all probe and jig capacitance

Figure 5.

#### **EXPANDED LOGIC DIAGRAM**



# TIMING DIAGRAM (Q<sub>A</sub> Connected to Clock B)



#### **APPLICATIONS INFORMATION**

Each half of the MC54/74HC390A has independent  $\div$  2 and  $\div$  5 sections (except for the Reset function). The  $\div$  2 and  $\div$  5 counters can be connected to give BCD or bi–quinary (2–5) count sequences. If Output  $Q_A$  is connected to the Clock B input (Figure 4), a decade divider with BCD output is obtained. The function table for the BCD count sequence is given in Table 1.

To obtain a bi–quinary count sequence, the input signals connected to the Clock B input, and output  $Q_D$  is connected to the Clock A input (Figure 5).  $Q_A$  provides a 50% duty cycle output. The bi–quinary count sequence function table is given in Table 2.

Table 1. BCD Count Sequence\*

	Output					
Count	Q <sub>D</sub>	Q <sub>C</sub>	Q <sub>B</sub>	$Q_A$		
0	L	L	L	L		
1	L	L	L	Н		
2	L	L	Н	L		
3	L	L	Н	Н		
4	L	Н	L	L		
5	L	Н	L	Н		
6	L	Н	Н	L		
7	L	Н	Н	Н		
8	Н	L	L	L		
9	Н	L	L	Н		

<sup>\*</sup>Q<sub>A</sub> connected to Clock B input.

Table 2. Bi-Quinary Count Sequence\*\*

		Output				
Count	$Q_A$	$Q_D$	Q <sub>C</sub>	Q <sub>B</sub>		
0	L	L	L	L		
1	L	L	L	Н		
2	L	L	Н	L		
3	L	L	Н	Н		
4	L	Н	L	L		
8	H	L	L	L		
9.	H	L	L	Н		
10	H	L	Н	L		
1311	CH	L	Н	Н		
12	Н	Н	L	L		

<sup>\*\*</sup> QD connected to Clock A input.

#### **CONNECTION DIAGRAMS**

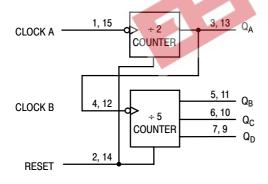


Figure 6. BCD Count

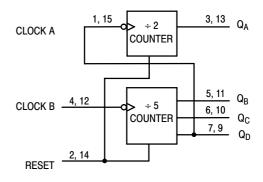
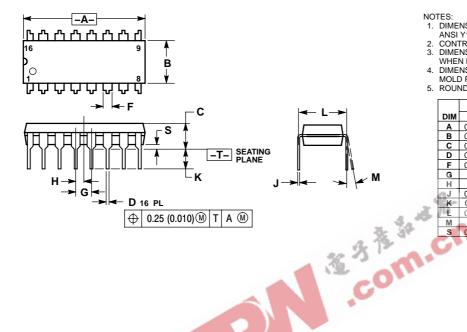


Figure 7. Bi-Quinary Count

#### **PACKAGE DIMENSIONS**

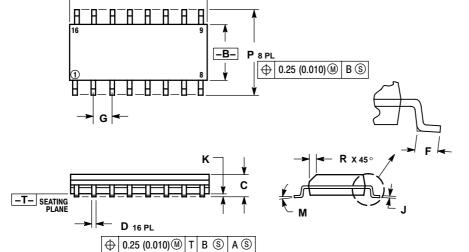
PDIP-16 **N SUFFIX** CASE 648-08 **ISSUE T** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOULD BLASUL.
- MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100	BSC	2.54	BSC
Н	0.050	BSC	1.27	BSC
₫J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
140	0.295	0.305	7.50	7.74
M	_ 0°	10 °	0°	10 °
S	0.020	0.040	0.51	1.01





-A-

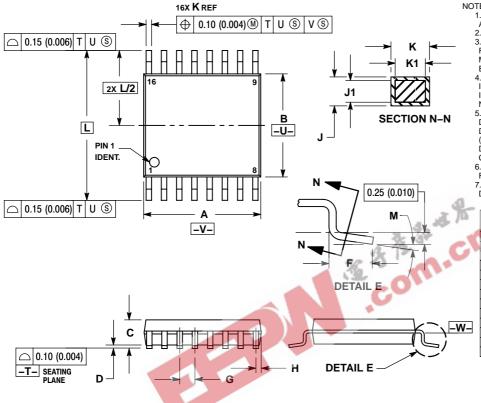
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.
- CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR.

- PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION SHALL BE 0.127 (0.005) TOTAL
  IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

#### **PACKAGE DIMENSIONS**

TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE A** 



#### NOTES:

- OTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

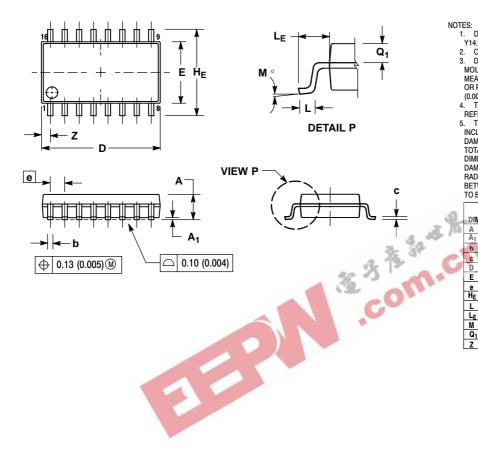
  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. SHALL NOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
М	0 °	8°	0 °	8°

#### PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX** CASE 966-01 **ISSUE O** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  I. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT, MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LΕ	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.78		0.031

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